

## 2-Vrms Cap-Less Line Driver with Adjustable Gain

#### **Features**

- Operation Voltage: 3V to 3.6V
- Cap-less Output
  - Eliminates Output Capacitors
  - Improves Low Frequency Response
  - Reduces POP/Clicks
- Low Noise and THD
  - Typical SNR 107dB
  - Typical Vn 7uVrms
  - Typical THD+N < 0.02%
- Maximum Output Voltage Swing into 2.5k Load
  - 2Vrms at 3.3V Supply Voltage
- single-ended Input
- External Gain Setting from 1V/V to 10V/V
- Fast Start-up Time: 0.5ms
- Integrated De-Pop Control
- Thermal Protection
- Less External Components Required
- +/-8kV IEC ESD Protection at line outputs

## **Applications**

- LCD / PDP TVs
- CD / DVD players
- Set-Top Boxes
- Home Theater in Box

## **Description**

The AD22657B is a 2-Vrms cap-less stereo line driver. The device is ideal for single supply electronics. Cap-less design can eliminate output dc-blocking capacitors for better low frequency response and save cost.

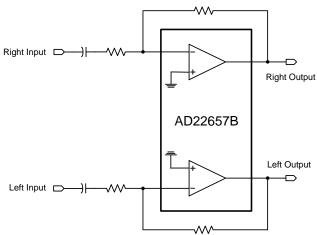
The AD22657B is capable of delivering 2-Vrms output into a  $10k\Omega$  load with 3.3V supply. The gain settings can be set by users from 1V/V to 10V/V externally. The AD22657B build-in shutdown control and de-pop control sequence also help AD22657B to be a pop-less device.

The AD22657B is available in a 10-pin MSOP package.

## **Ordering Information**

Product ID	Package	Packing	Comments
AD22657B-MH10NAT		80 Units / Tube	
AD22037 B-IVITI TUINAT	MSOP-10	100 Tubes / Small Box	Green(HF)
AD22657B-MH10NAR		3k Units Tape & Reel	

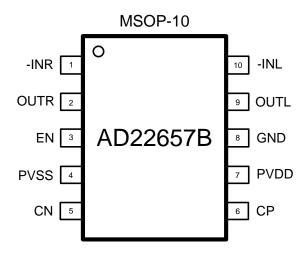
## **Simplified Application Circuit**



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# **Pin Assignments**



# **Pin Description**

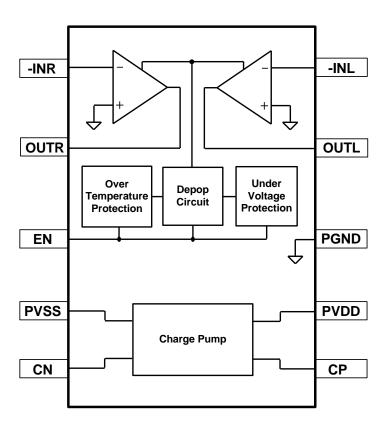
No.	Name	Type <sup>(1)</sup>	Pin Description
1	-INR	I	Right channel OP negative input
2	OUTR	0	Right channel OP output
3	EN	I	Enable input, active high
4	PVSS	Р	Supply voltage
5	CN	I/O	Charge-pump flying capacitor negative terminal
6	СР	I/O	Charge-pump flying capacitor positive terminal
7	PVDD	Р	Positive supply
8	GND	Р	Ground
9	OUTL	0	Left channel OP output
10	-INL	I	Left channel OP negative input

<sup>(1)</sup> I=input, O=output, P=power

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## **Functional Block Diagram**



**Available Package** 

Package Type	Device No.	<b>Θ</b> <sub>ja</sub> (℃/W) <sup>(1)</sup>	<b>Θ</b> <sub>jc</sub> (℃/W) <sup>(2)</sup>
MSOP-10	AD22657B	120	45

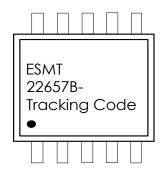
<sup>(1)</sup>  $\Theta_{ja}$  is measured at room temperature (TA=25°C), natural convection environment test board, which is constructed with a thermal efficient,

## **Marking Information**

AD22657B

Line 1: LOGO

Line 2 : Product No.
Line 3 : Tracking Code



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<sup>2-</sup>layers PCB. The measurement is tested using the JEDEC51-3 thermal measurement standard.

<sup>(2)</sup>  $\Theta_{jc}$  represents the heat resistance for the heat flow between the chip and package's top surface.



**Absolute Maximum Ratings** (1)

SYMBOL	PARAMETER	VALUE	UNIT
	Supply Voltage, V <sub>DD</sub> to GND	-0.3 to 3.6	٧
V <sub>I</sub>	Input Voltage	VSS -0.3 to VDD+0.3	V
$R_L$	Minimum load impedance	> 600	Ω
	EN to GND	-0.3 to VDD+0.3	V
T <sub>stg</sub>	Storage temperature range	-65 to 150	$^{\circ}\!\mathbb{C}$
TJ	Maximum operating junction temperature range	-40 to 150	$^{\circ}\!\mathbb{C}$

<sup>(1)</sup> The absolute maximum ratings are limiting values of operation, safety of the device cannot be guaranteed if beyond those values.

**Recommended Operating Conditions** 

SYMBOL	PARAMETER		Min	NOM	Max	UNIT
$V_{DD}$	Supply Voltage		3.0	3.3	3.6	V
V <sub>IH</sub>	High Level Input Voltage EN			60		% of $V_{\text{DD}}$
$V_{IL}$	Low Level Input Voltage EN			40		% of $V_{\text{DD}}$
T <sub>A</sub>	Operating Ambient Temperature Range		-40		85	$^{\circ}\!\mathbb{C}$
$R_L$	Load Resistance		600			Ω

#### **Electrical Characteristics**

SYMBOL	PARAMETER	TEST CONDITIONS	Min	NOM	Max	UNIT
I <sub>DD</sub>	V <sub>DD</sub> Supply Current	EN=V- <sub>DD</sub>		7	15	mA
I <sub>SD</sub>	V <sub>DD</sub> Shutdown Current	EN=0V, V <sub>DD</sub> =3.3V			5	μΑ
II	Input Current	EN pin		0.1		μΑ
Vo	Output Voltage	THD+N=1%, V <sub>DD</sub> =3.3V,	2.0	2.3		Vrms
v <sub>o</sub>	(Outputs In Phase)	f <sub>IN</sub> =1kHz	2.0	2.3		VIIIIS
THD+N	Total Harmonic	V <sub>O</sub> =2Vrms, f <sub>IN</sub> =1kHz		0.004		%
THUTIN	Distortion Plus Noise	V0-2VIIII3, I N-1KI12		0.004		70
Crosstalk	Channel Separation	V <sub>O</sub> =2Vrms, f <sub>IN</sub> =1kHz		98		dB
$V_N$	Output Noise	R <sub>I</sub> =10k, R <sub>F</sub> =10k		7	15	μVrms

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# **Electrical Characteristics (Con't)**

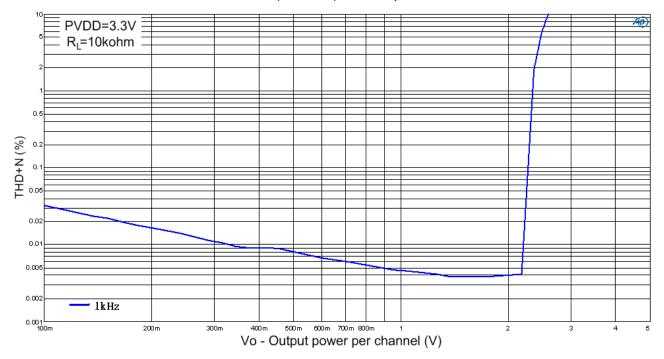
SYMBOL	PARAMETER TEST CONDITIONS		Min	NOM	Max	UNIT
$V_{SR}$	Slew Rate			8		V/µs
SNR	Signal to Noise Ratio	$V_0$ =2Vrms, $R_I$ =10k, $R_F$ =10k, A-weighted		107		dB
$G_{BW}$	Unit-Gain Bandwidth			8		MHz
A <sub>VO</sub>	Open-Loop Gain		80			dB
Vos	Output Offset Voltage	V <sub>DD</sub> =3V to 3.6V, Input Grounded	-1		1	mV
PSRR	Power Supply Rejection Ratio	$V_{DD}$ =3V to 3.6V, $V_{rr}$ =200mVrms, $f_{IN}$ =1kHz		-80	-60	dB
Rı	Input Resistor Range		1	10	47	kΩ
R <sub>F</sub>	Feedback Resistor Range		4.7	20	100	kΩ
f <sub>CP</sub>	Charge-Pump Frequency		400	500	600	kHz
	Maximum capacitive Load			220		pF
TSD	Over Temperature Protection Level			150		$^{\circ}\! \mathbb{C}$
T <sub>start-up</sub>	Start-up Time			0.5		ms

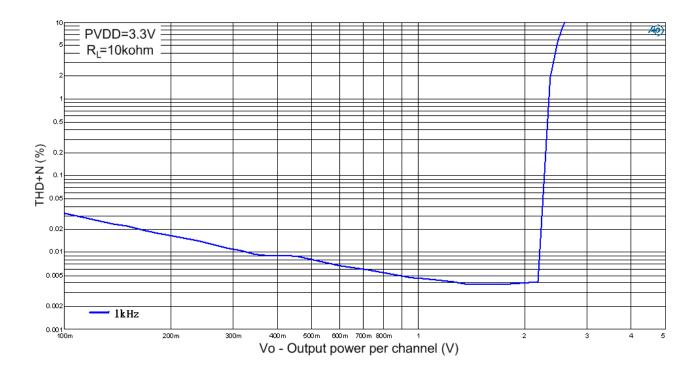
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## **Typical Characteristics**

• Total Harmonic Distortion + Noise (THD+N) vs. Output Power

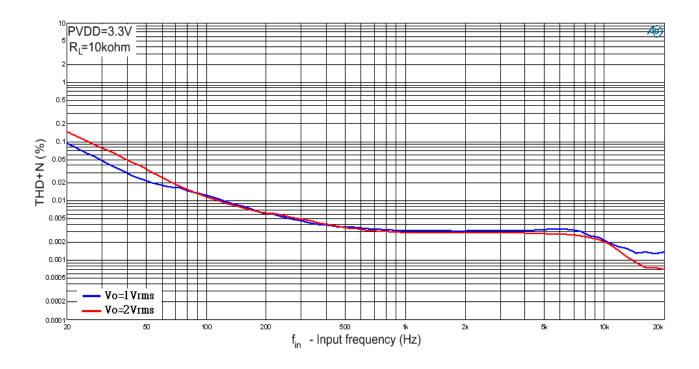


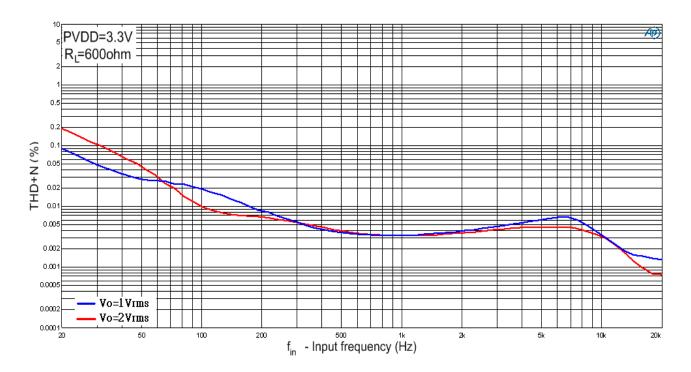


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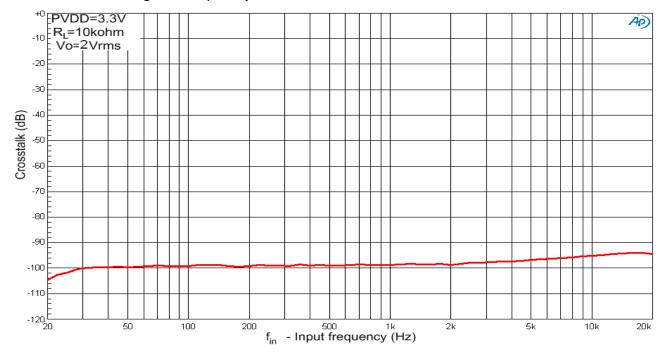
• Total Harmonic Distortion + Noise (THD+N) vs. Signal Frequency



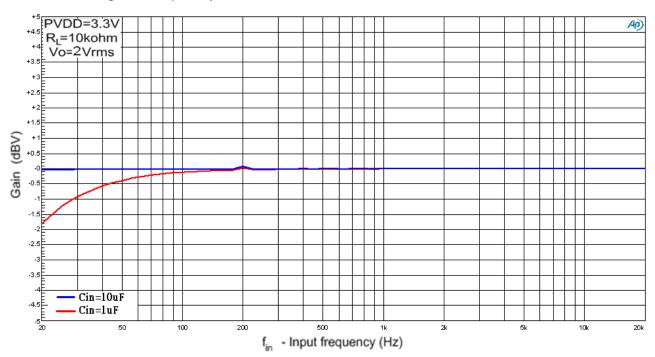




# • Crosstalk vs. Signal Frequency



## • Gain vs. Signal Frequency





## **Application Information**

#### **Line Driver Amplifiers Operation**

A conventional inverting line-driver amplifier always requires an output dc-blocking capacitor and a bypass capacitor, see Figure 1. DC blocking capacitors are large in size and cost a lot. It also restricts the output low frequency response. POP will occur if the charge and discharge processes on output capacitors are not carefully take cared. Besides, it needs to wait for a long time to charge V<sub>OUT</sub> from 0V to VDD/2.

For a cap-less line driver, see figure 2, a negative supply voltage (-VDD) is produced by the integrated charge-pump, and feeds to line driver's negative supply instead of ground. The positive input can directly connect to ground without a CBYPASS, and VOUT is biased at ground which can eliminate the output dc-blocking capacitors. The output voltage swing is doubled compared to conventional amplifiers.

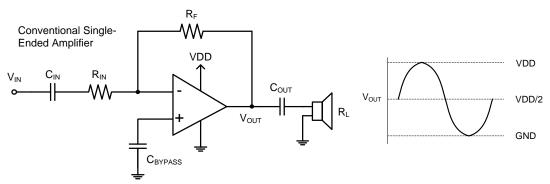


Figure 1. Conventional Line Driver Amplifier

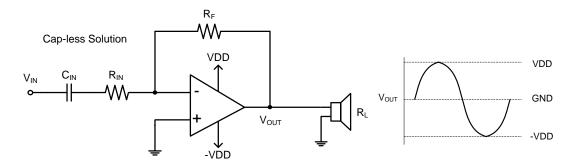


Figure 2. Cap-less Line Driver Amplifier



#### ■ Charge-Pump Operation

The charge-pump is used to generate a negative supply voltage to supply to line-driver. It needs two external capacitors,  $C_{\text{FLY}}$  and  $C_{\text{PVSS}}$ , for normal operation, see figure 3 (a). The operation can be analyzed with two phase. In phase I, see figure 3 (b),  $C_{\text{FLY}}$  is charged to PVDD, and in phase II, see figure 3 (c), the charges on  $C_{\text{FLY}}$  are shared with  $C_{\text{PVSS}}$ , that makes PVSS a negative voltage. After an adequate clock cycles, PVSS will be equaled to -PVDD. Low ESR capacitors are recommended, and the typical value of  $C_{\text{FLY}}$  and  $C_{\text{PVSS}}$  is  $1\mu\text{F}$ . A smaller capacitance can be used, but the maximum output voltage may be reduced.

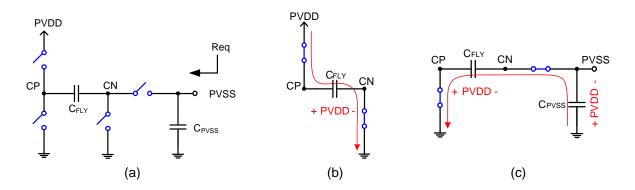


Figure 3. Charge-Pump Operation

#### ■ Enable Function

The enable function is used to reduce power consumption while the device is not in use. When a logic low is applied to this pin, the overall circuits are turned off. Line driver output and PVSS are pulled to ground. When a logic high is applied to enable pin, the PVSS is started to build-up and line driver output signal is released after about 0.5ms typically.

#### ■ Decoupling Capacitors

A low ESR power supply decoupling capacitor is required for better performance. The capacitor should place as close to chip as possible, the value is typically  $1\mu F$ . For filtering low frequency noise signals, a  $10\mu F$  or greater capacitor placed near the chip is recommended.

#### ■ Input Blocking Capacitors (C<sub>IN</sub>)

An input blocking capacitor is required to block the dc voltage of the audio source and allows the input to bias at a proper dc level for optimum operation. The input capacitor and input resistor (R<sub>I</sub>) form a high-pass filter with the corner frequency determined as following equation:

$$f_C = \frac{1}{2\pi R_I C_{IN}}$$



#### ■ Gain Setting Resistors (R<sub>I</sub> and R<sub>F</sub>)

The line driver's gain is determined by  $R_I$  and  $R_F$ . The configuration of the amplifier is inverting type, see figure 4. The gain equation is listed as follows:

Inverting configuration:  $A_V = -\frac{R_F}{R_I}$ 

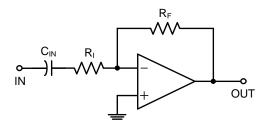


Figure 4. Line Driver Amplifier Configurations

The values of  $R_I$  and  $R_F$  must be chosen with consideration of stability, frequency response and noise. The recommended value of  $R_I$  is in the range from  $1k\Omega$  to  $47k\Omega$ , and  $R_F$  is from  $4.7k\Omega$  to  $100k\Omega$  for. The gain is in the range from -1V/V to -10V/V for inverting configuration. Table 1 lists the recommended resistor values for different configurations.

$R_i(k\Omega)$	$R_F(k\Omega)$	Inverting Input Gain (V/V)
22	22	-1
15	30	-2
33	68	-2.1
10	100	-10

Table 1. Recommended Resistor Values

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#### **Second-Order Filter Configuration**

AD22657B can be used like a standard OPAMP. Several filter topologies can be implemented by using AD22657B, single-ended input configuration, see figure 5. For inverting input configuration, the overall gain is  $-\frac{R2}{R1}$ , the high-pass filter's cutoff frequency is  $\frac{1}{2\pi R1C3}$ , the low-pass filter's cutoff frequency

is  $\frac{1}{2\pi\sqrt{R2R3C1C2}}$  , The detail component values are listed on table 2.

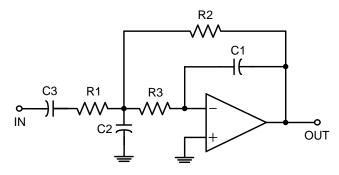


Figure 5. Second-order Active Low-Pass Filter

Gain (V/V)	High Pass (Hz)	Low Pass (kHz)	C1 (pF)	C2 (pF)	C3 (µF)	R1 (kΩ)	R2 (kΩ)	R3 (kΩ)
-1	1.6	40	100	680	10	10	10	24
-1.5	1.3	40	68	680	15	8.2	12	30
-2	1.6	60	33	150	6.8	15	30	47
-2	1.6	30	47	470	6.8	15	30	43
-3.33	1.2	30	33	470	10	13	43	43
-10	1.5	30	22	1000	22	4.7	47	27

Table 2. Second-order Low-Pass Filter Specifications

#### **Over-Temperature Protection**

AD22657B provide an over-temperature protection to limit the junction temperature to 150℃. As junction temperature exceeds 150°C, internal thermal sensor will turn off the drivers immediately. The drivers will turn on again if the junction temperature is smaller than 130°C. A 20°C hysteresis is designed to lower the average junction temperature during continuous thermal overload conditions, increasing lifetime of the chip.

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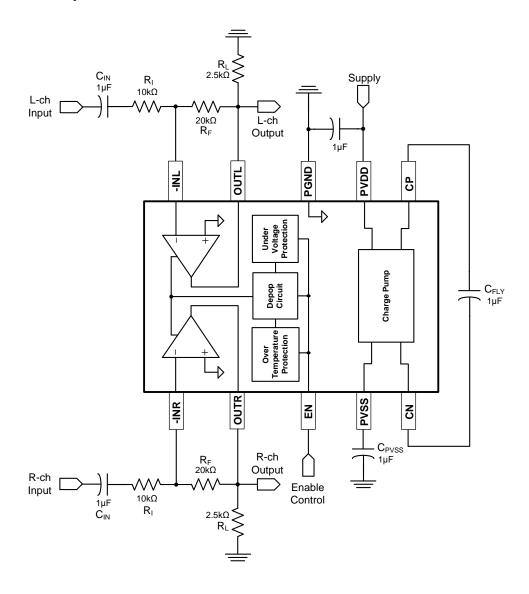
Elite Semiconductor Microelectronics Technology Inc.

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# **Typical Application Circuit**

## **■** Line Driver Amplifier

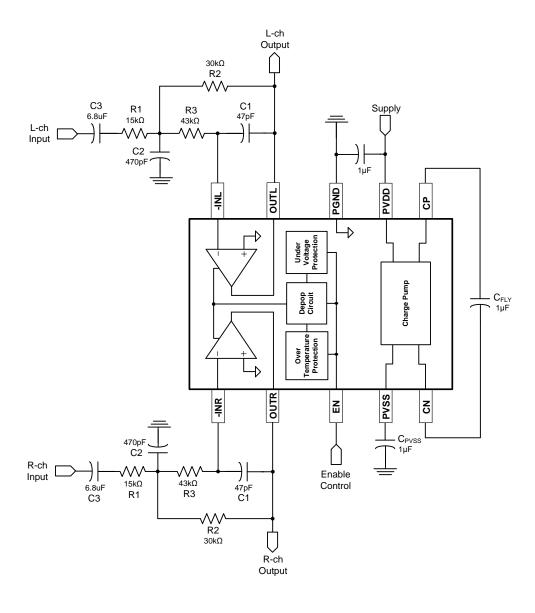


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# **Typical Application Circuit (cont.)**

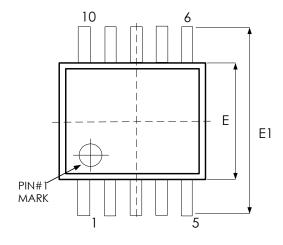
■ Second-Order Active Low-Pass Filter (load support >= 600Ω only)

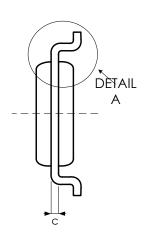


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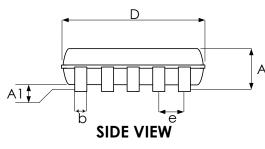


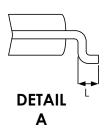
# Package Outline Drawing MSOP-10











Cryssla ol	Dimension in mm				
Symbol	Min	Max			
А	0.81	1.10			
A1	0.00	0.15			
Ъ	0.17	0.33			
С	0.08	0.23			
D	2.90	3.10			
Е	2.90	3.10			
E1	4.80	5.00			
е	0.50 BSC				
L	0.40 0.80				



# **Revision History**

Revision	Date	Description
0.1	2014.06.17	Initial version
0.2	2017.12.25	Update typical application circuit.
0.3	2018.04.13	Update Features.

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